

查询"DG1M3A"供应商

## DG1M3A

30V 1.5A

### 特長

- 超小型SMD
- 超薄型=0.8mm
- 低 $V_F=0.46V$
- 低 $I_R=0.05mA$
- $I_{FSM}=30A$

### Feature

- Ultra-small SMD
- Ultra-thin PKG=0.8mm
- Low  $V_F=0.46V$
- Low  $I_R=0.05mA$
- $I_{FSM}=30A$

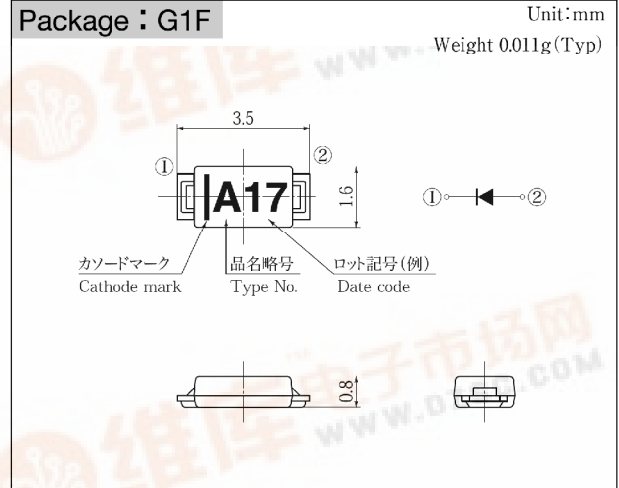
### 用途

- バッテリー逆接防止
- DC/DCコンバータ

### Main Use

- Reverse connect protection for DC power source
- DC/DC Converter

### ■外觀図 OUTLINE



外形図については新電元Webサイト又は〈ダイオードカタログ・技術資料編〉を参照下さい。捺印表示については捺印仕様をご確認下さい。  
For details of the outline dimensions, refer to our web site or the diode technical data book. As for the marking, refer to the specification "Marking, Terminal Connection".

### ■定格表 RATINGS

#### ●絶対最大定格 Absolute Maximum Ratings (指定のない場合 $T_l=25^\circ C$ )

項目 Item	記号 Symbol	条件 Conditions	品名 Type No.	DG1M3A	単位 Unit	
保存温度 Storage Temperature	$T_{stg}$			-55~150	$^\circ C$	
接合部温度 Operation Junction Temperature	$T_j$			150	$^\circ C$	
せん頭逆電圧 Maximum Reverse Voltage	$V_{RM}$			30	V	
出力電流 Average Rectified Forward Current	$I_O$	50Hz正弦波, 抵抗負荷 50Hz sine wave, Resistance load	$T_a=32^\circ C$	*1	1.0	A
			$T_a=37^\circ C$	*2	1.5	
せん頭サージ順電流 Peak Surge Forward Current	$I_{FSM}$	50Hz正弦波, 非繰り返し1サイクルせん頭値, $T_j=25^\circ C$ 50Hz sine wave, Non-repetitive 1 cycle peak value, $T_j=25^\circ C$		30	A	

#### ●電氣的・熱的特性 Electrical Characteristics (指定のない場合 $T_l=25^\circ C$ )

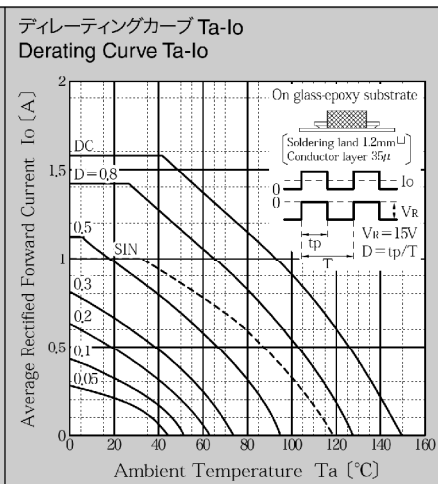
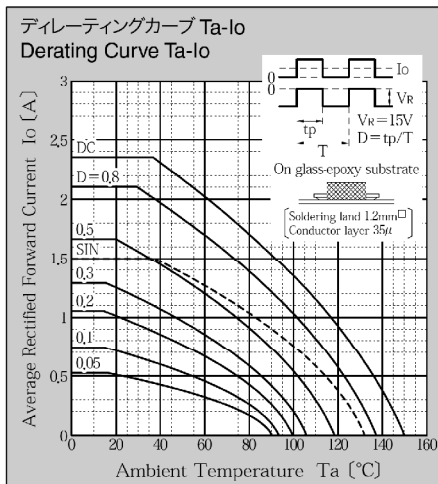
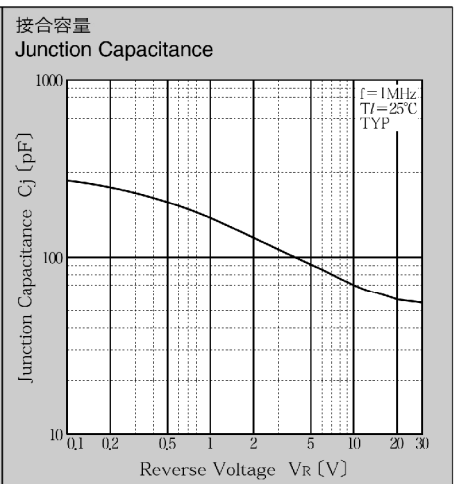
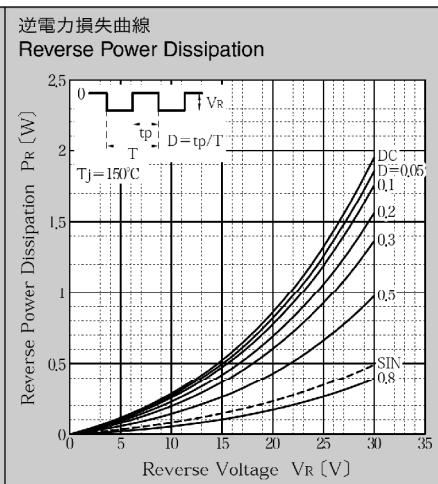
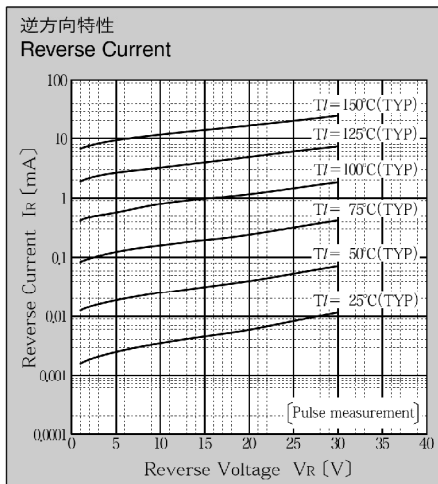
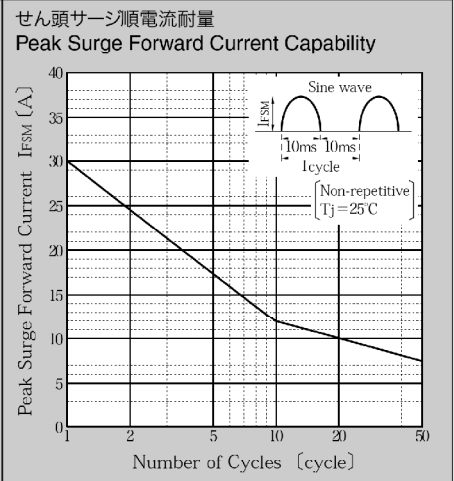
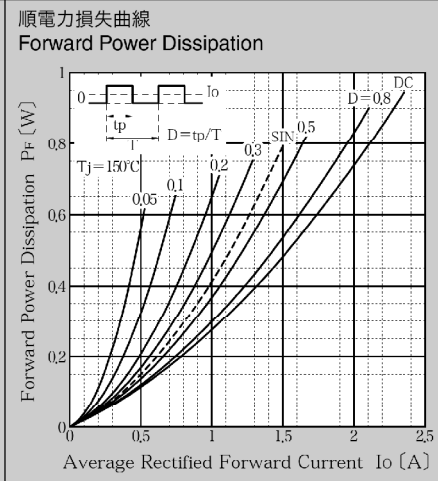
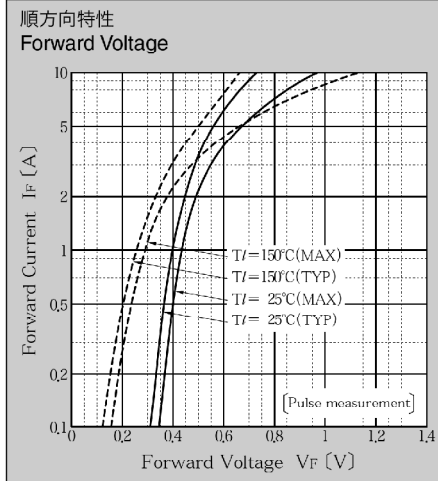
順電圧 Forward Voltage	$V_F$	$I_F=0.5A$ , パルス測定 Pulse measurement	MAX 0.40	V	
		$I_F=1.5A$ , パルス測定 Pulse measurement	MAX 0.46		
逆電流 Reverse Current	$I_R$	$V_R=V_{RM}$ , パルス測定 Pulse measurement	MAX 0.05	mA	
接合容量 Junction Capacitance	$C_j$	$f=1MHz, V_R=10V$	TYP 70	pF	
熱抵抗 Thermal Resistance	$\theta_{ja}$	接合部・周囲間 Junction to ambient	*1	MAX 210	$^\circ C/W$
			*2	MAX 120	
	$\theta_{jl}$	接合部・リード間 Junction to lead	*3	MAX 20	

- \*1 1インチプリント基板 (パターン32.6mm<sup>2</sup>)  
Measured on 1 x 1 inch substrate (pattern area : 32.6mm<sup>2</sup>)
- \*2 1インチプリント基板 (パターン160mm<sup>2</sup>)  
Measured on 1 x 1 inch substrate (pattern area : 160mm<sup>2</sup>)
- \*3 2インチアルミナ基板 (パターン2,100mm<sup>2</sup>)  
Measured on 2 x 2 inch alumina substrate (pattern area : 2,100mm<sup>2</sup>)

Small SMD

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■特性图 CHARACTERISTIC DIAGRAMS



\*1インチプリント基板 (パターン160mm<sup>2</sup>)  
Measured on 1 x 1 inch substrate (pattern area 160mm<sup>2</sup>)

\*1インチプリント基板 (パターン32.6mm<sup>2</sup>)  
Measured on 1 x 1 inch substrate (pattern area 32.6mm<sup>2</sup>)

\* Sine waveは50Hzで測定しています。  
 \* 50Hz sine wave is used for measurements.  
 \* 半導体製品の特性は一般的にバラツキを持っています。  
 \* Typical is a statistical average of the device's ability.  
 \* Semiconductor products generally have characteristic variation.  
 \* Typical is a statistical average of the device's ability.